

FEATURES

- LOW LEAKAGE: 0.25 PA TYPICAL
- LOW INPUT CAPACITANCE: 2.0 PF TYPICAL
- HIGH INPUT IMPEDANCE

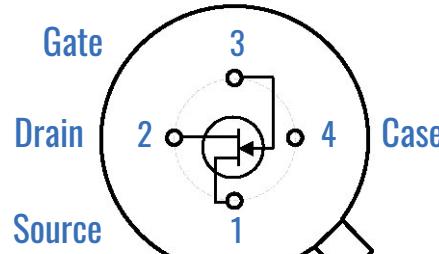
DESCRIPTION

The -50V 2N4117/A, 2N4118/A, and 2N4119/A JFET's are targeted for ultra high input impedance applications for mid to high frequency designs. Gate leakages are typically 1pA at room temperatures.

The 2N4117 has a cutoff voltage of less than 1.8V ideal for low-level power supplies.

The TO-72 package is hermetically sealed and suitable for military applications.

TX, TXV, and S-Level Screening Available - Consult Factory.



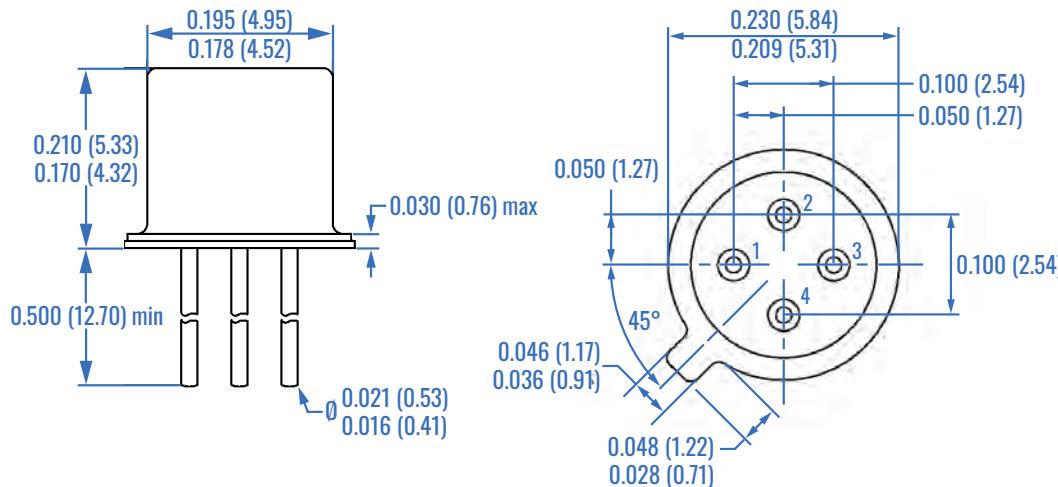
Bottom View

ORDERING GUIDE

Part Number 2N4117, 2N4117A, 2N4118, 2N4118A, 2N4119, 2N4119AA
Description -50V N-Channel JFET

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Reverse Gate Source and Gate Drain Voltage	V_{RGS}	-40	V
Continuous Forward Gate Current	I_{FG}	50	mA
Continuous Device Power Dissipation	P_D	300	mW
Power Derating	P	2	mW/°C
Operating Junction Temperature	T_J	-55 to 125	°C
Storage Temperature	T_{STG}	-65 to 150	°C



STATIC CHARACTERISTICS

Typical @ 25°C unless otherwise noted, highlighted values = A version.

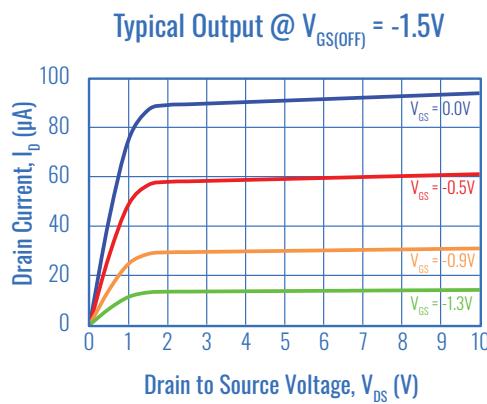
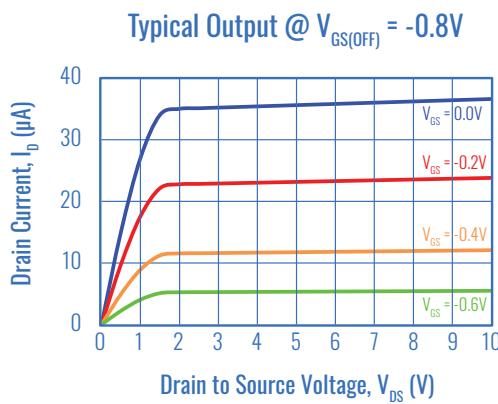
Parameter	Symbol	2N4117/A		2N4118/A		2N4119/A		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Gate to Source Breakdown Voltage	$V_{DS} = 0V, I_G = -1\mu A$	$V_{(BR)GSS}$	-40		-40		-40	V
Gate to Source Reverse Current	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSS}		-10		-10		-10 pA
				-1		-1		-1 pA
Gate to Source Cutoff Voltage	$V_{DS} = 10V, I_D = 1nA$	$V_{GS(OFF)}$	-0.6	-1.8	-1	-3	-2	-6 V
Drain to Source Saturation Current	$V_{GS} = 0V, V_{DS} = 10V$ (Pulsed)	I_{DSS}	0.03	0.09	0.08	0.24	0.2	0.6 pA
			0.015	0.09	0.08	0.24	0.2	0.6 pA

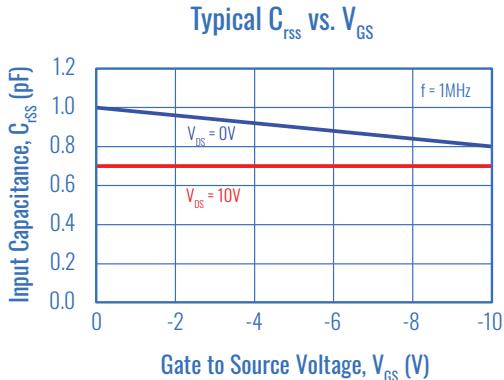
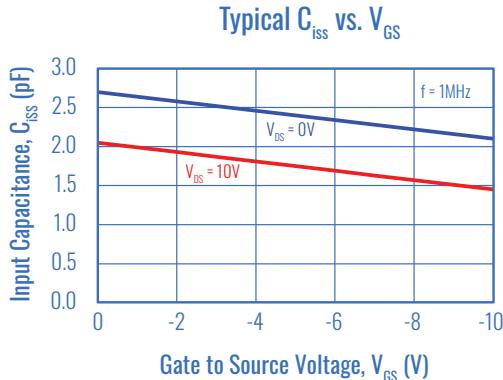
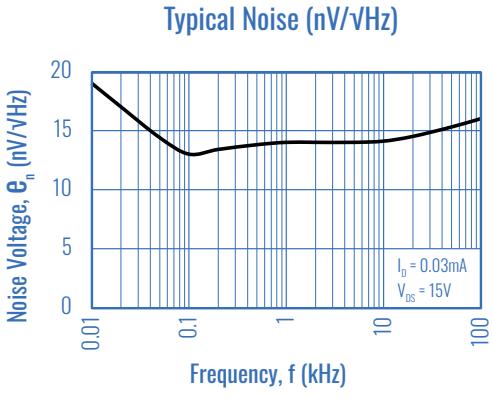
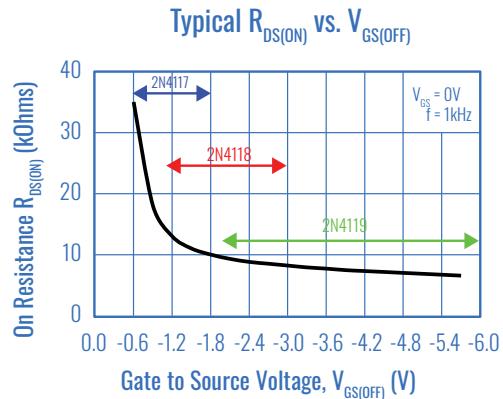
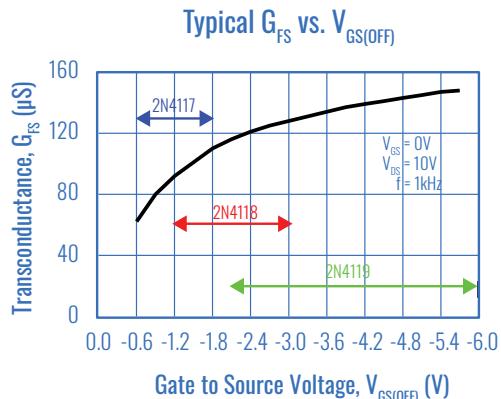
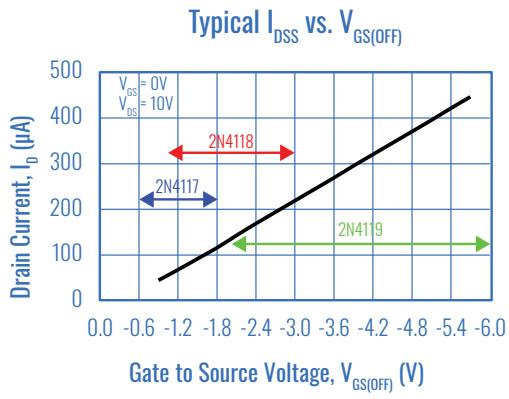
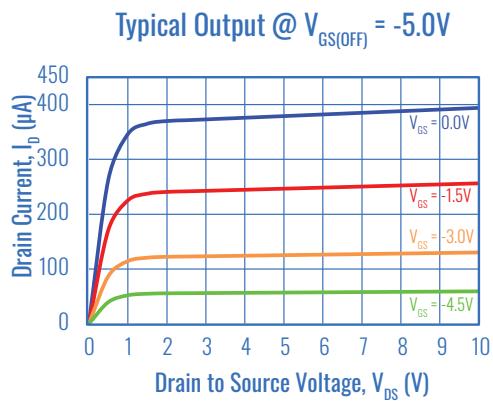
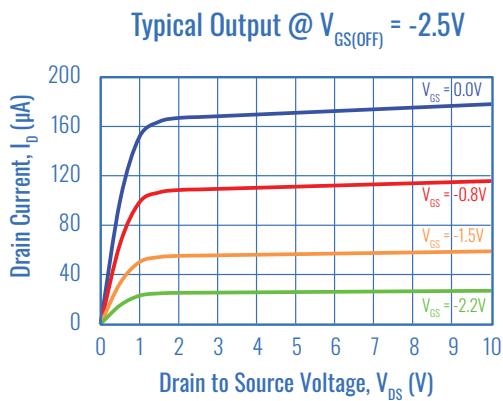
DYNAMIC CHARACTERISTICS

Typical @ 25°C unless otherwise noted

Parameter	Symbol	2N4117/A		2N4118/A		2N4119/A		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Forward Transconductance	$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$	G_{FS}	70	210	80	250	100	330 μS
Output Conductance	G_{DS}			3		5		10 μS
Input Capacitance	C_{iss}			3		3		3 pF
Reverse Transfer Capacitance	C_{rss}			1.5		1.5		1.5 pF

TYPICAL PERFORMANCE CHARACTERISTICS





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